

DATA SHEET

RG2006LN — Diffused Junction Silicon Diode Low VF · High-Speed Switching Diode

Features

- High breakdown voltage ($V_{RRM}=600V$).
- High reliability.
- One-point fixing type plastic mold package facilitating easy mounting and heat dissipation.
- Fast reverse recovery time.
- Low noise at the time of reverse recovery.

Specifications

Absolute Maximum Ratings at $T_a=25^\circ C$

| Parameter | Symbol | Conditions | Ratings | Unit |
|--|-----------|---|-------------|------------|
| Repetitive Peak Reverse Voltage | V_{RRM} | | 600 | V |
| Nonrepetitive Peak Reverse Surge Voltage | V_{RSM} | | 600 | V |
| Average Output Current | I_O | | 20 | A |
| Peak Output Current | I_{OP} | $PW \leq 100\mu s$, duty cycle $\leq 50\%$ | 40 | A |
| Surge Forward Current | I_{FSM} | Sine wave, 10ms | 180 | A |
| Junction Temperature | T_j | | 150 | $^\circ C$ |
| Storage Temperature | T_{stg} | | -55 to +150 | $^\circ C$ |

Electrical Characteristics at $T_a=25^\circ C$

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|-----------------------|---------------|----------------------------------|---------|------|------|----------------|
| | | | min | typ | max | |
| Reverse Voltage | V_R | $I_R=1mA$ | 600 | | | V |
| Forward Voltage | V_{F1} | $I_F=10A$ | | 1.45 | 1.6 | V |
| | V_{F2} | $I_F=20A$ | | 1.8 | 2.1 | V |
| Reverse Current | I_R | $V_R=600V$ | | | 100 | μA |
| Reverse Recovery Time | t_{rr1} | $I_F=10A$, $di / dt=100A/\mu s$ | | | 50 | ns |
| | t_{rr2} | $I_F=0.5A$, $I_R=1A$ | | 16 | | ns |
| Thermal Resistance | $R_{th(j-c)}$ | Junction-Case : Smoothed DC | | | 3.22 | $^\circ C / W$ |

Package Dimensions

unit : mm (typ)

7509-004

